

2SJ244

Silicon P Channel MOS FET

REJ03G0853-0200

(Previous: ADE-208-1187)

Rev.2.00 Sep 07, 2005

Description

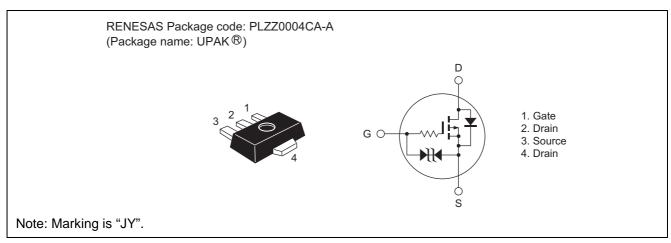
High speed power switching

Low voltage operation

Features

- Very Low on-resistance
- High speed switching
- Suitable for camera or VTR motor drive circuit, power switch, solenoid drive and etc.

Outline



*UPAK is a trademark of Renesas Technology Corp.

Absolute Maximum Ratings

 $(Ta = 25^{\circ}C)$

Item	Symbol	Value	Unit
Drain to source voltage	V _{DSS}	-12	V
Gate to source voltage	V_{GSS}	±7	V
Drain current	I _D	±2	Α
Drain peak current	I _{D (pulse)} Note 1	±4	A
Channel dissipation	Pch Note 2	1	W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

Notes: 1. PW \leq 100 μ s, duty cycle \leq 10%

2. Value on the alumina ceramic board (12.5 \times 20 \times 0.7 mm)

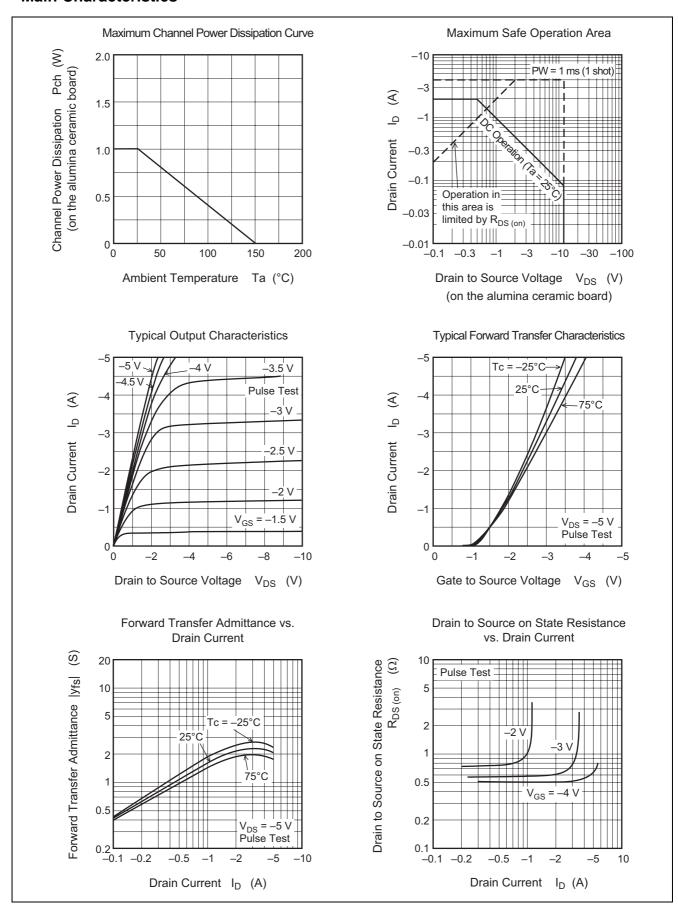
Electrical Characteristics

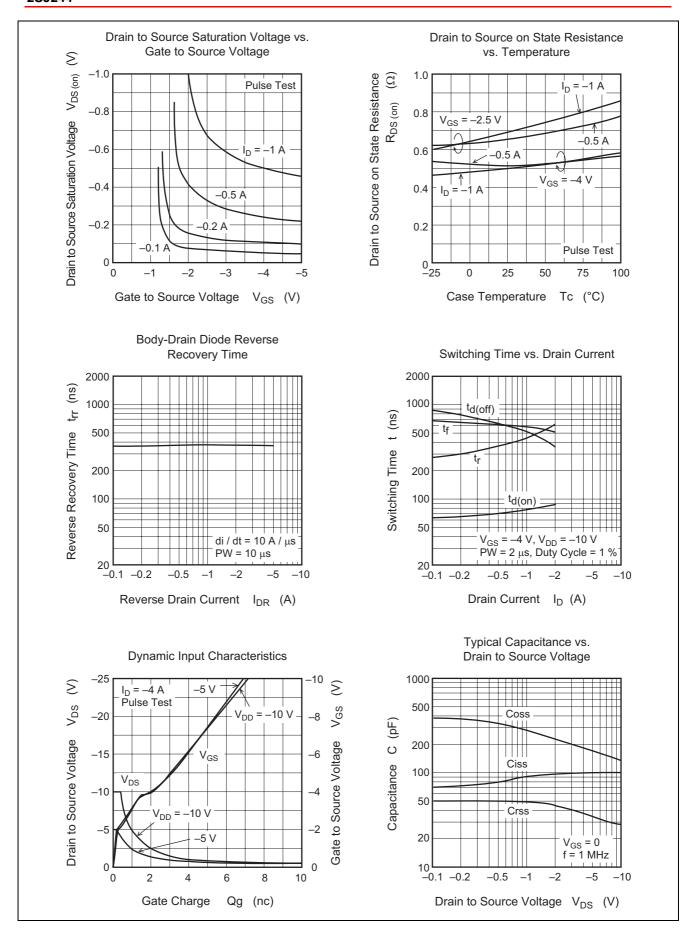
 $(Ta = 25^{\circ}C)$

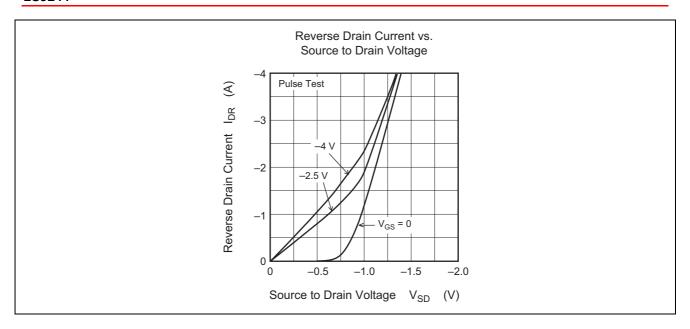
Item	Symbol	Min	Тур	Max	Unit	Test Conditions
Drain to source breakdown voltage	V _{(BR) DSS}	-12	_	_	V	$I_D = -1 \text{ mA}, V_{GS} = 0$
Gate to source breakdown voltage	V _{(BR) GSS}	±7	_	_	V	$I_G = \pm 10 \ \mu A, \ V_{DS} = 0$
Gate to source leak current	I _{GSS}	_	_	±5	μΑ	$V_{GS} = \pm 6 \text{ V}, V_{DS} = 0$
Zero gate voltage drain current	I _{DSS}	_	_	-1	μΑ	$V_{DS} = -8 \text{ V}, V_{GS} = 0$
Gate to source cutoff voltage	V _{GS (off)}	-0.4	_	-1.4	V	$I_D = -100 \ \mu A, \ V_{DS} = -5 \ V$
Static drain to source on state resistance	R _{DS (on) 1}	_	0.65	0.9	Ω	$I_D = -0.5 \text{ A}, V_{GS} = -2.5 \text{ V}^{\text{Note 3}}$
	R _{DS (on) 2}	_	0.5	_	Ω	$I_D = -1 A, V_{GS} = -4 V^{\text{Note 3}}$
Forward transfer admittance	y _{fs}	_	1.8	_	S	$I_D = -1 A, V_{DS} = -5 V^{\text{Note 3}}$
Input capacitance	Ciss	_	100	_	pF	$V_{DS} = -5 V$
Output capacitance	Coss	_	168	_	pF	$V_{GS} = 0$
Reverse transfer capacitance	Crss	_	35	_	pF	f = 1 MHz
Turn-on delay time	t _{d (on)}	_	365	_	ns	$I_D = -0.2 \text{ A}^{\text{Note 3}}$
Turn-off delay time	t _{d (off)}	_	1450	_	ns	Vin = -4 V, $R_L = 51 \Omega$
Body to drain diode forward voltage	V_{DF}	_	_	7	V	$I_F = 4 \text{ A}^{\text{Note 3}}, V_{GS} = 0$

Note: 3. Pulse test

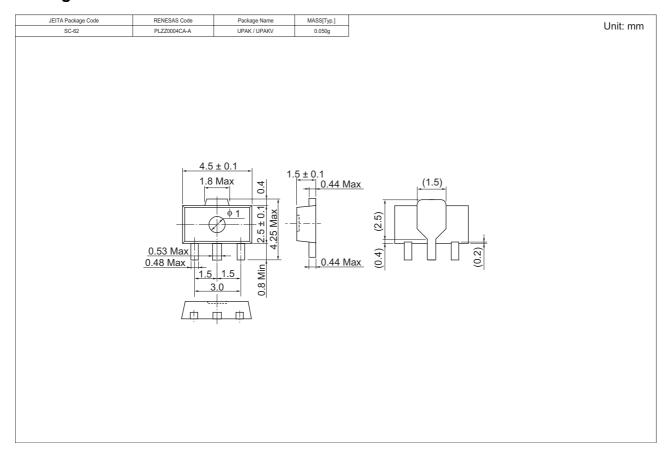
Main Characteristics







Package Dimensions



Ordering Information

Part Name	Quantity	Shipping Container
2SJ244JYTL-E	1000 pcs	Taping
2SJ244JYTR-E	1000 pcs	Taping

Note: For some grades, production may be terminated. Please contact the Renesas sales office to check the state of production before ordering the product.

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